

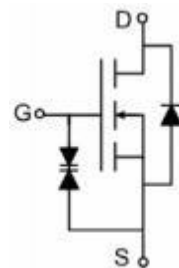
N-Channel Enhancement Mode Power MOSFET

General Features

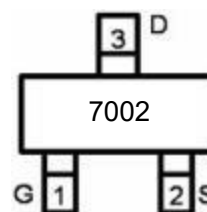
- $V_{DS} = 60V, I_D = 0.3A$
 $R_{DS(ON)} < 3\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 2.2\Omega @ V_{GS}=10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package
- ESD Rating: HBM $\geq 1500V$

Application

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
7002	2N7002	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150^\circ C$)	I_D	0.3	A
		0.19	
Drain Current-Pulsed (Note 1)	I_{DM}	0.8	A
Maximum Power Dissipation	P_D	0.35	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1	uA
		V _{GS} =±20V, V _{DS} =0V	-		±10	uA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.55	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =0.2A	-	1.93	3	Ω
		V _{GS} =10V, I _D =0.3A	-	1.75	2.2	Ω
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =0.2A	0.1	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	10	21	50	PF
Output Capacitance	C _{oss}		-	11	25	PF
Reverse Transfer Capacitance	C _{rss}		-	4.2	5	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =0.2A V _{GS} =10V, R _{GEN} =10Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	50	-	nS
Turn-Off Delay Time	t _{d(off)}		-	17	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =10V, I _D =0.3A, V _{GS} =4.5V	-	1.7	3	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	0.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical And Thermal Characteristics

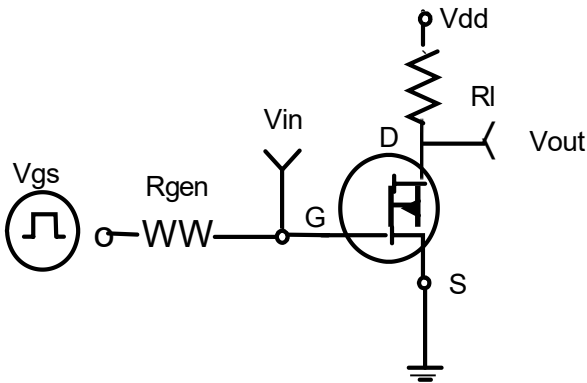


Figure 1: Switching Test Circuit

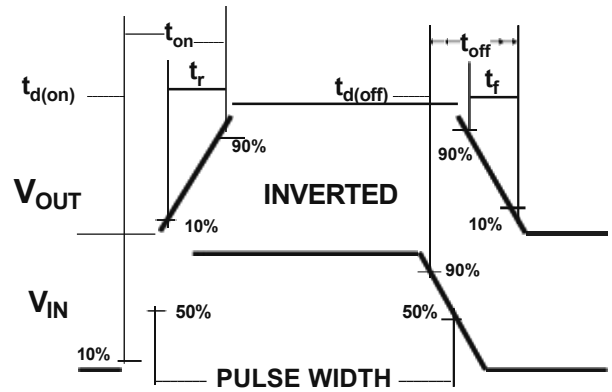


Figure 2: Switching Waveforms

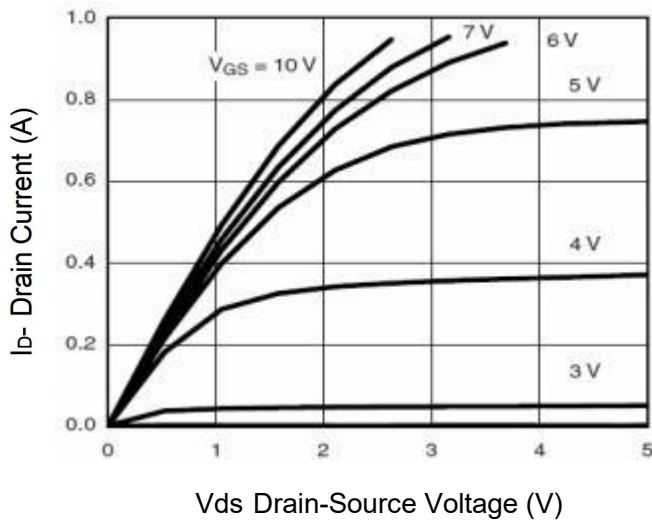


Figure 3 Output Characteristics

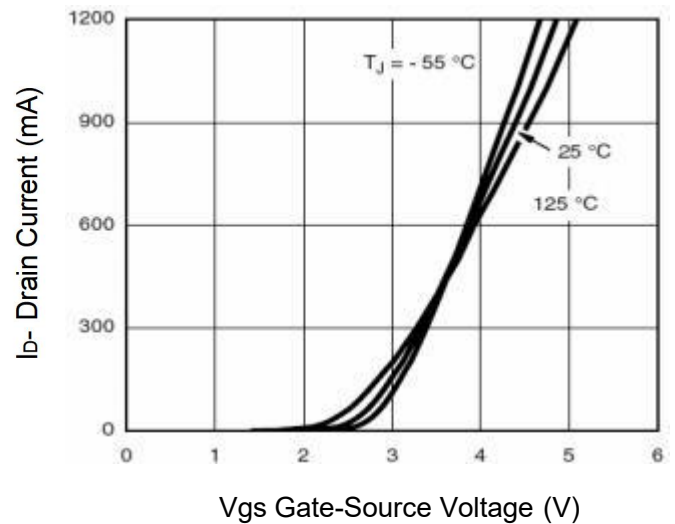


Figure 4 Transfer Characteristics

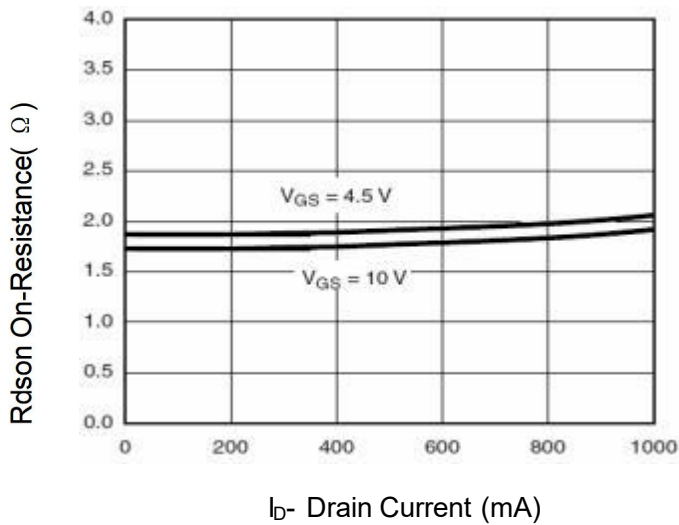


Figure 5 Drain-Source On-Resistance

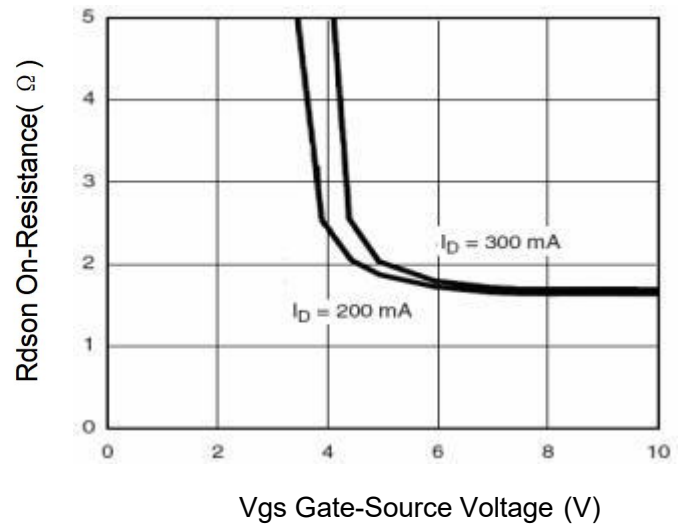
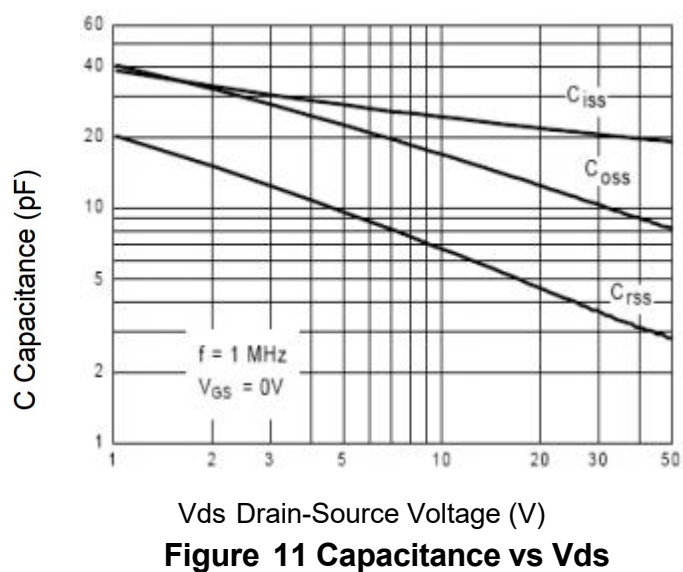
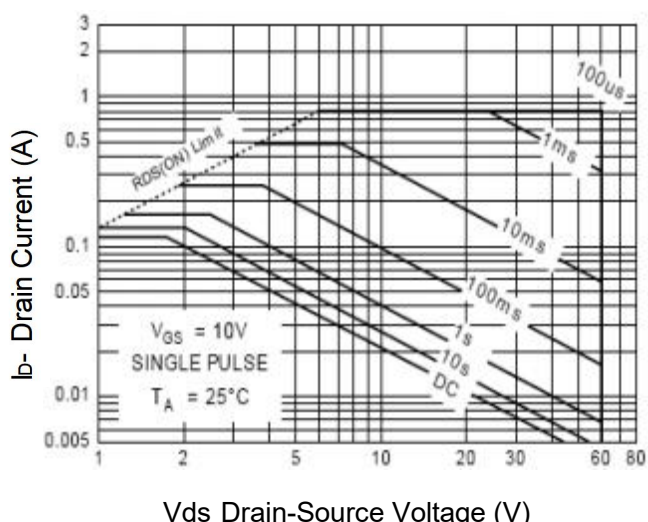
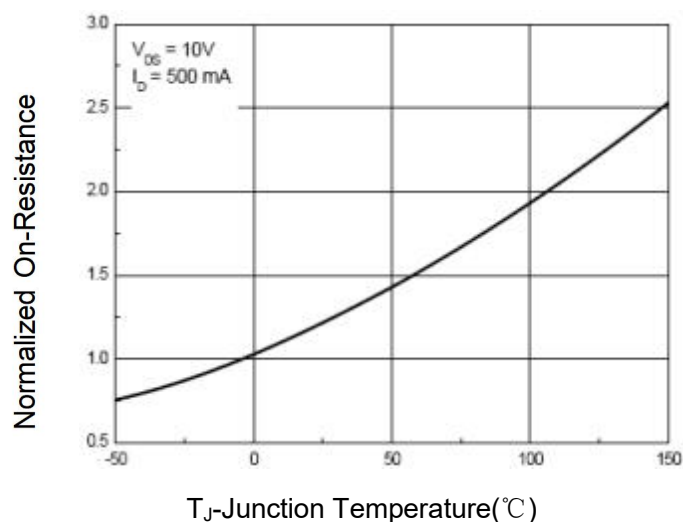
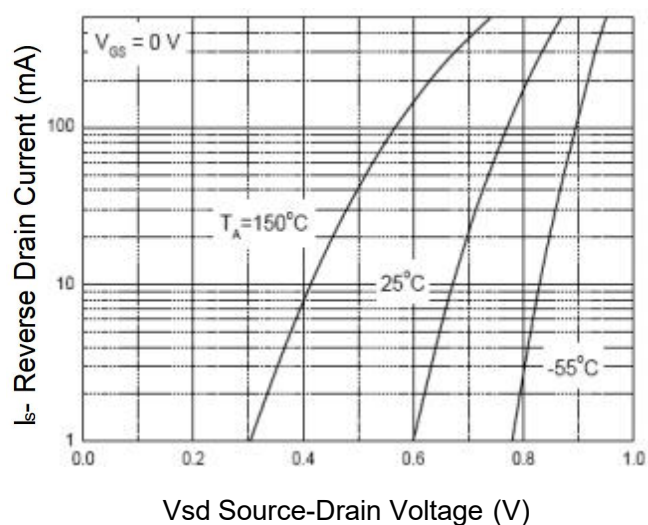
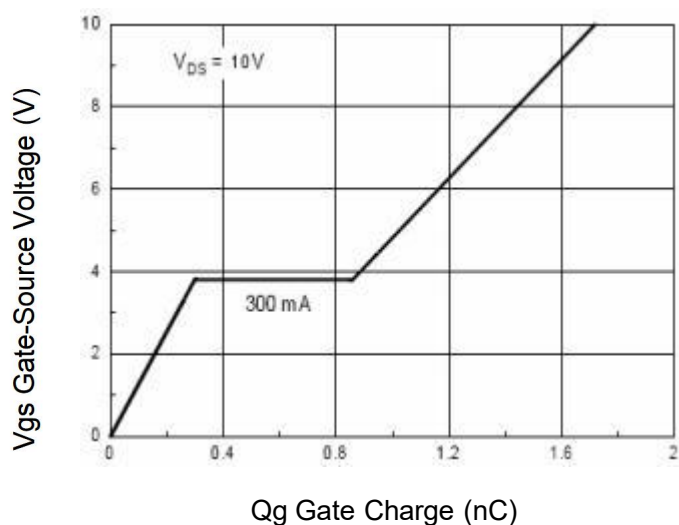


Figure 6 Rdson vs Vgs



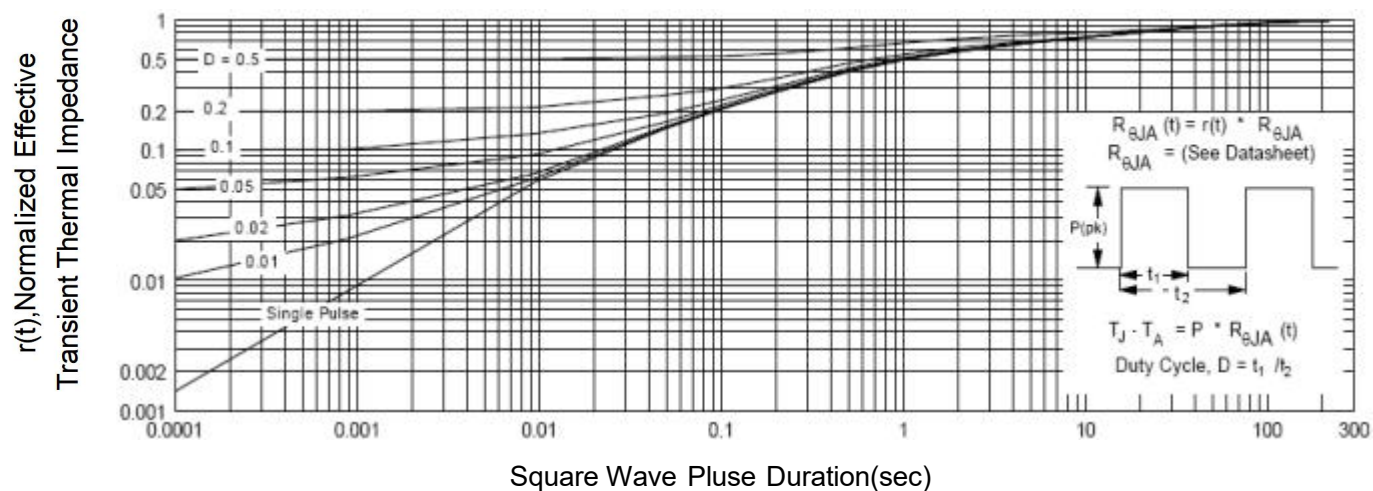


Figure 12 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information

